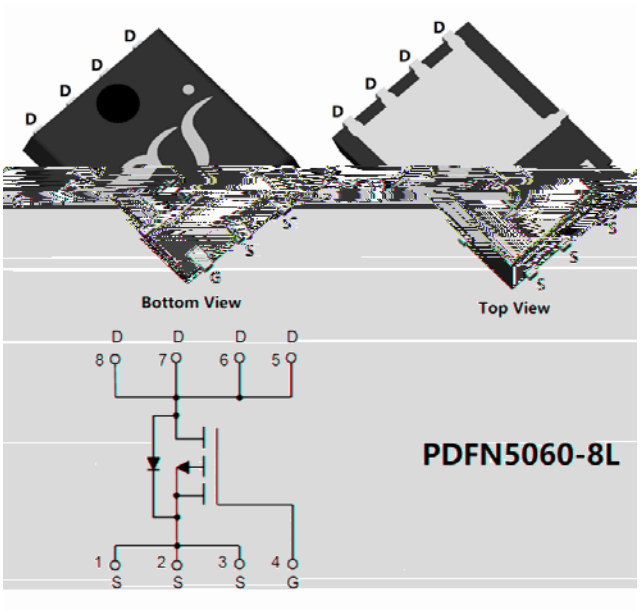
P-Channel Enhancement Mode Field Effect Transistor



Product Summary

General Description

Applications

Absolute Maximum Ratings

Parameter		Symbol	Limit	Unit

Thermal resistance

Parameter		Symbol	Typ	Max	Units

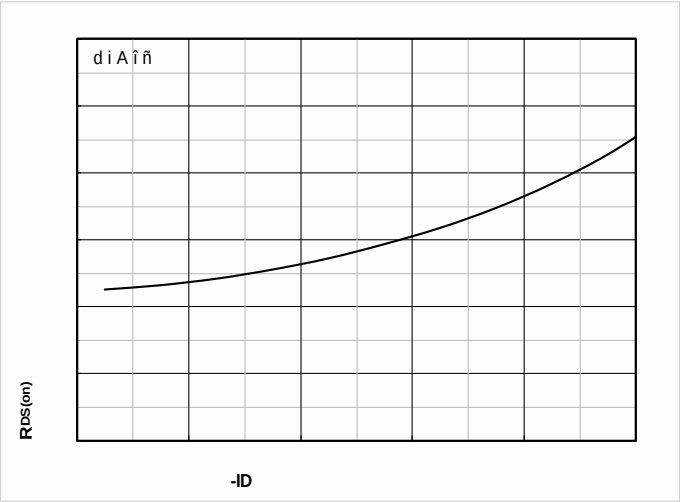
YJG122GP10HHQ

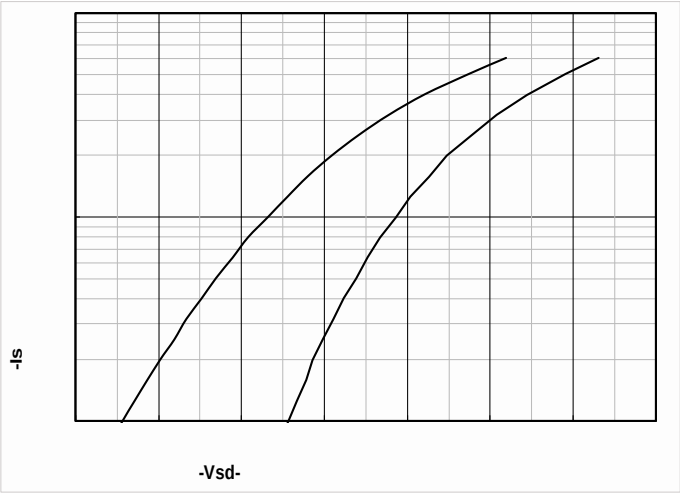
Ordering Information

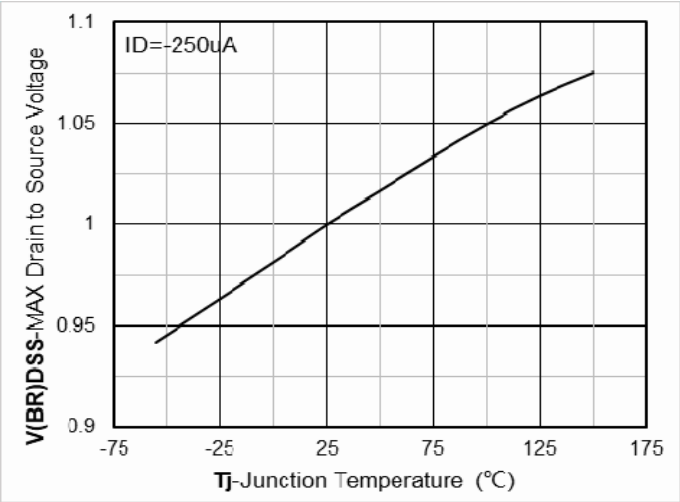
PREFERED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE

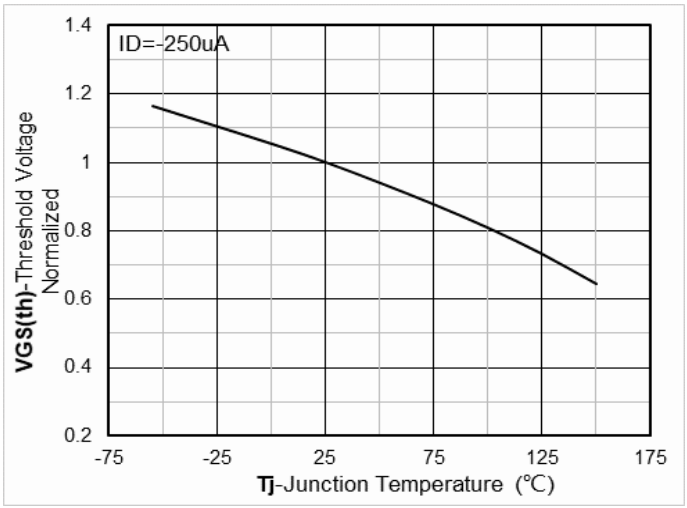
Electrical Characteristics

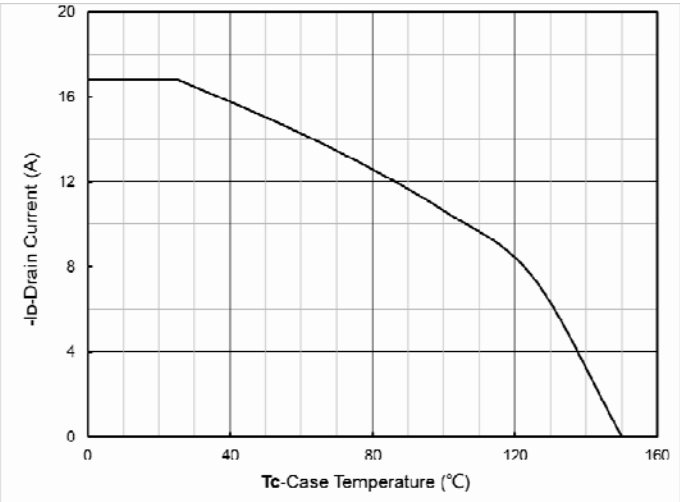
Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Dynamic Parameters						
Switching Parameters						

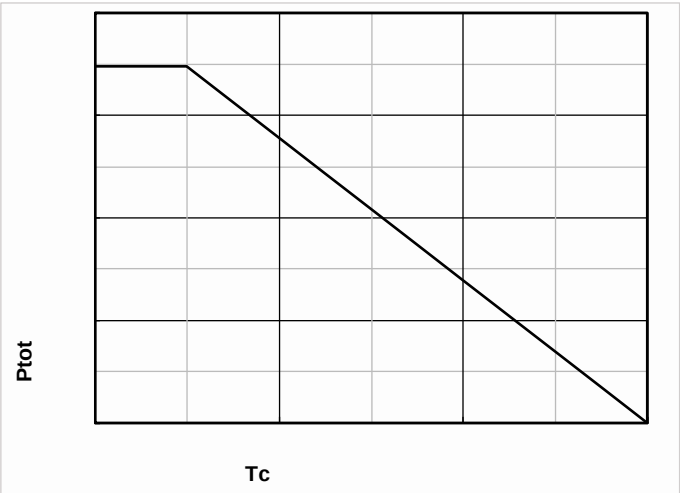

diAîñ
RDS(on)
-ID

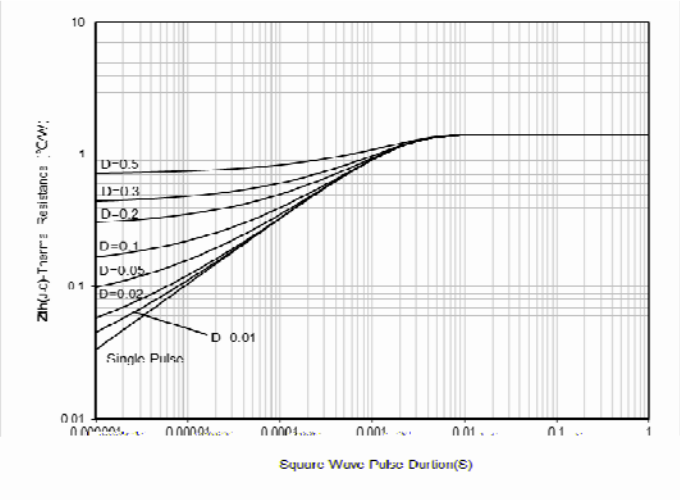

-Is
-Vsd-

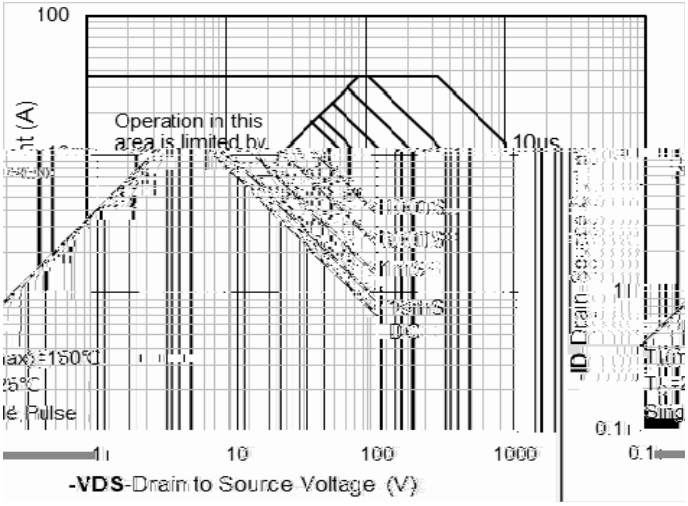

ID=-250uA
V(BR)DSS-MAX Drain to Source Voltage
1.1
1.05
1
0.95
0.9
-75
-25
25
75
125
175
Tj-Junction Temperature (℃)


ID=-250uA
VGS(th)-Threshold Voltage Normalized
1.4
1.2
1
0.8
0.6
0.4
0.2
-75
-25
25
75
125
175
Tj-Junction Temperature (℃)

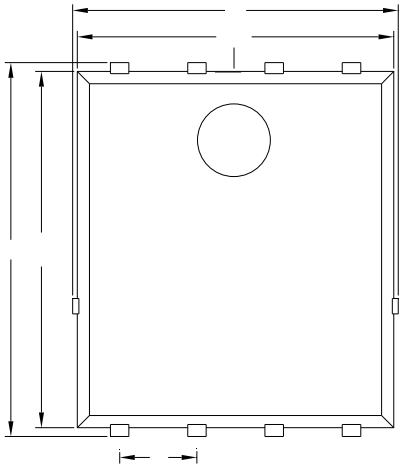

-ID-Drain Current (A)
20
16
12
8
4
0
0
40
80
120
160
Tc-Case Temperature (℃)

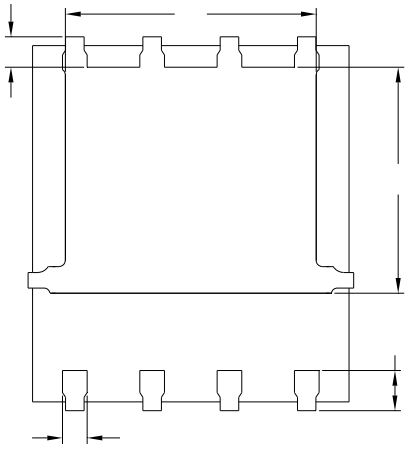

Ptot
Tc

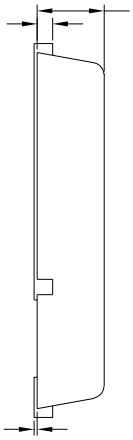

10
1
0.1
0.01
D=0.5
D=0.3
D=0.2
D=0.1
D=0.05
D=0.02
D 0.01
Single Pulse
Square Wave Pulse Duration(S)

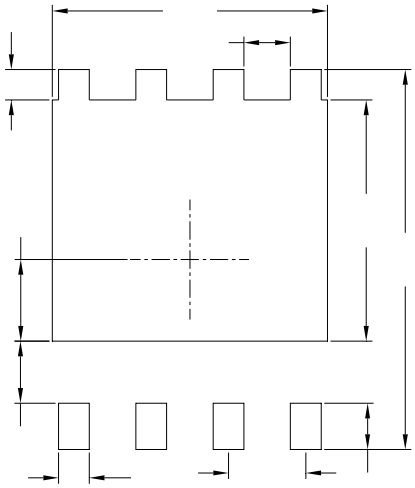

100
Operation in this
area is limited by
10us
1
10
100
1000
0.1
-VDS-Drain to Source Voltage (V)

Package information









Disclaimer